

**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

Part No. Y89KKG-KT84c(d)T

$I_{T(AV)}$	3800A
V_{DRM}, V_{RRM}	2000V 2200V
	2500V
t_q	40~120μs

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	$T_c=55^{\circ}\text{C}$	125			3800 A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$t_p=10\text{ms}$	125	1900			2500 V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			250 mA	
I_{TSM}	Surge on-state current	10ms half sine wave	125			44 kA	
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$	125			9680 $\text{A}^2\text{s} \times 10^3$	
V_{TO}	Threshold voltage		125			1.32 V	
r_T	On-state slope resistance					0.13 mΩ	
V_{TM}	Peak on-state voltage	$I_{TM}=5000\text{A}, F=70\text{kN}$	25			3.15 V	
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000 V/μs	
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}, \text{to}4000\text{A}$ Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$ Single pulse	125			1200 A/μs	
Q_{rr}	Recovery charge	$I_{TM}=2000\text{A}, t_p=4000\mu\text{s},$ $di/dt=-20\text{A}/\mu\text{s}, V_R=100\text{V}$	125		2100		μC
t_q	Circuit commutated turn-off time	$I_{TM}=2000\text{A}, t_p=4000\mu\text{s}, V_R=100\text{V}$ $dv/dt=30\text{V}/\mu\text{s}, di/dt=-20\text{A}/\mu\text{s}$	125	40		120 μs	
I_{GT}	Gate trigger current	$V_A=12\text{V}, I_A=1\text{A}$	25	40		450 mA	
V_{GT}	Gate trigger voltage			0.9		4.5 V	
I_H	Holding current			20		1000 mA	
I_L	Latching current					1000 mA	
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3 V	
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 70 kN				0.007 °C /W	
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.002 °C /W	
F_m	Mounting force			63		84 kN	
T_{vj}	Junction temperature			-40		125 °C	
T_{stg}	Stored temperature			-40		140 °C	
W_t	Weight				1390/ 1920		g
Outline		KT84c(d)T					

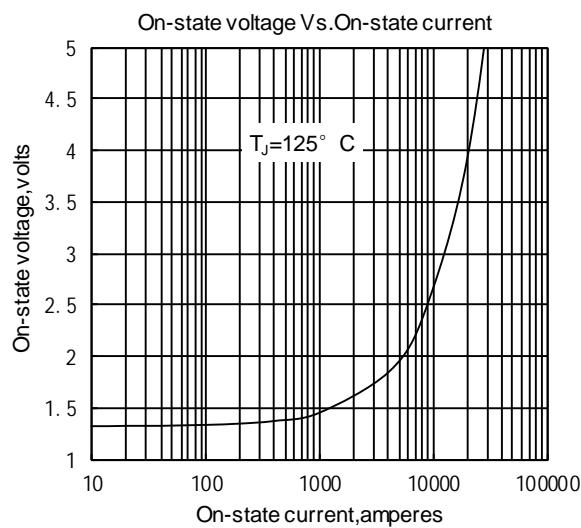


Fig.1

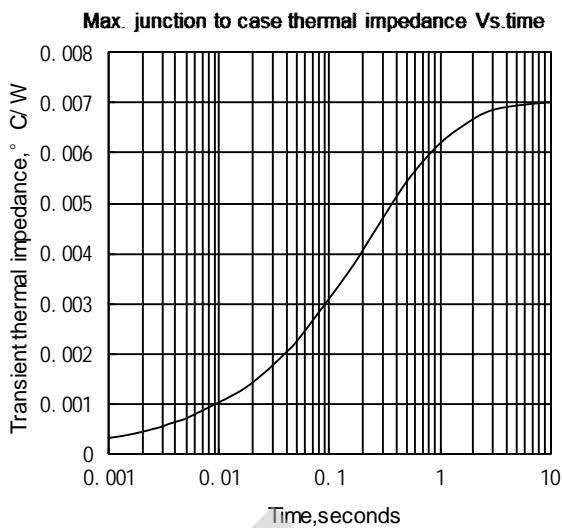


Fig.2

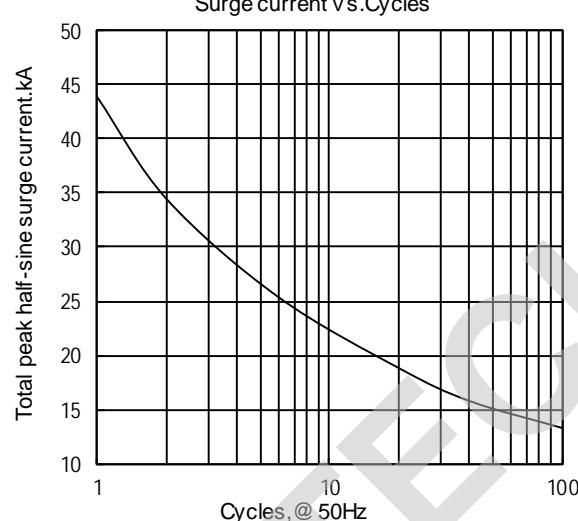


Fig.3

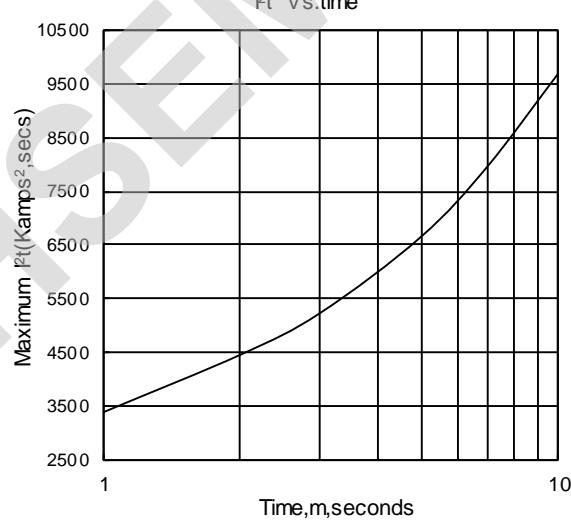


Fig.4

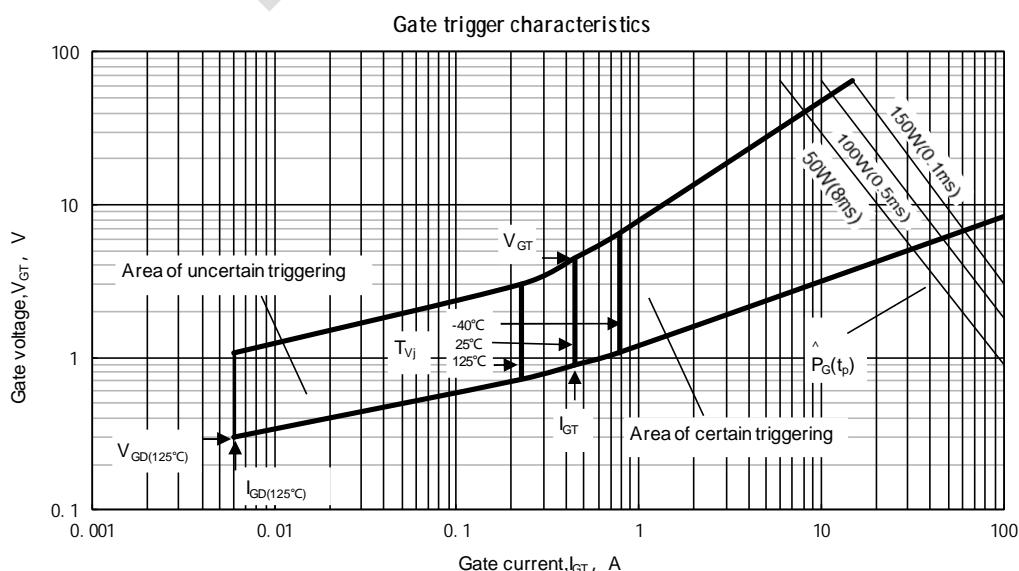
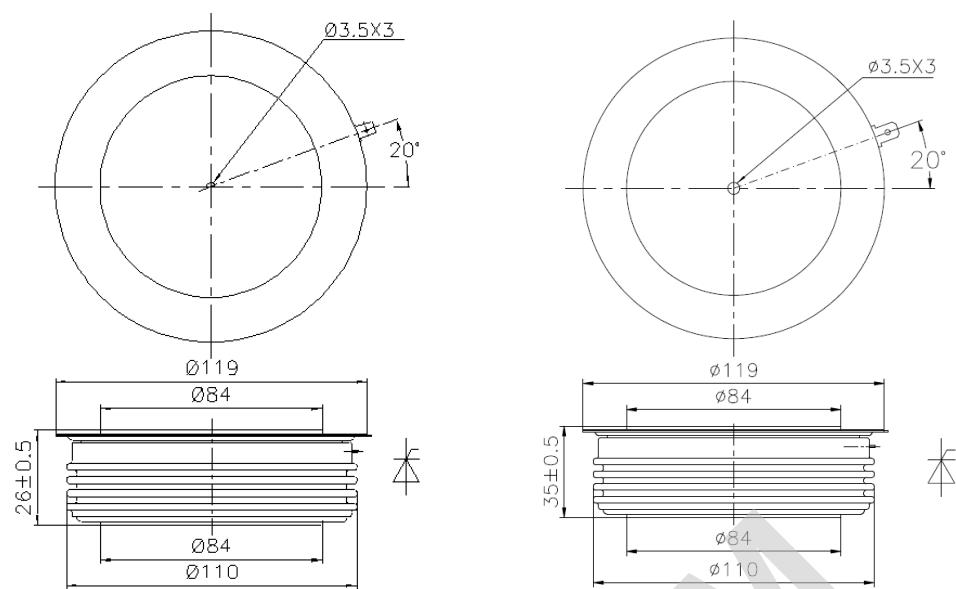


Fig.5

Outline:

TECHSEM reserves the right to change specifications without notice.